

PNP Epitaxial Planar Transistor

2SA1015

PNP EPITAXIAL PLANAR TRANSISTOR

Description

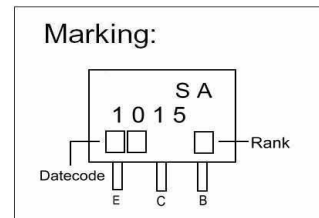
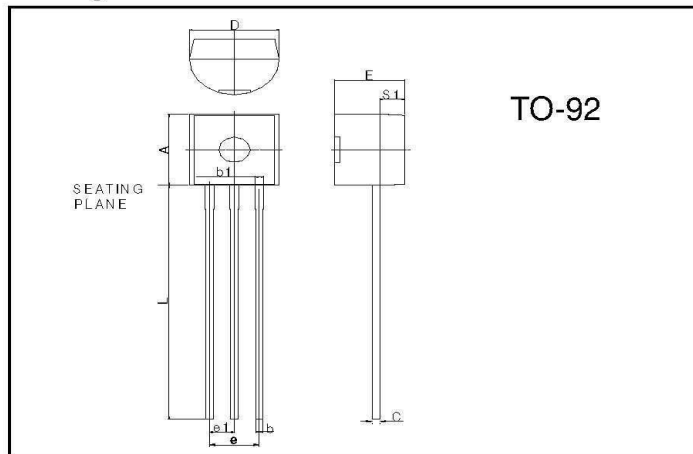
The 2SA1015 is designed for use in driver stage of AF amplifier and general purpose applications.

Features

*Collector-Base Voltage: $V_{CB0} = -50V$

*Complementary to 2SC1815

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ C$
Collector to Base Voltage	V_{CB0}	-50	V
Collector to Emitter Voltage	V_{CE0}	-50	V
Emitter to Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-150	mA
Base Current	I_B	-50	mA
Total Power Dissipation	P_D	400	mW

Characteristics at $T_a = 25^\circ C$

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V_{CB0}	-50	-	-	V	$I_C = -100\mu A, I_E = 0$
V_{CE0}	-50	-	-	V	$I_C = -1mA, I_B = 0$
V_{EB0}	-5	-	-	V	$I_E = -10\mu A, I_C = 0$
I_{CBO}	-	-	-100	nA	$V_{CE} = -50V, I_E = 0$
I_{EBO}	-	-	-100	nA	$V_{EB} = -5V, I_C = 0$
* $V_{CE(sat)}$	-	-	-0.3	V	$I_C = -100mA, I_B = -10mA$
* $V_{BE(sat)}$	-	-	-1.1	V	$I_C = -100mA, I_B = -10mA$
hFE1	70	-	700		$V_{CE} = -6V, I_C = -2mA$
hFE2	25	-	-		$V_{CE} = -6V, I_C = -150mA$
fT	80	-	-	MHz	$V_{CE} = -10V, I_C = -1mA, f = 100MHz$
Cob	-	-	7.0	pF	$V_{CB} = -10V, I_E = 0, f = 1MHz$

* Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Classification OF hFE1

Rank	O	Y	GR	L
Range	70-140	120-240	200-400	350-700



Data Sheet

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Characteristics Curve

